

| L Number | Hits  | Search Text   | DB                              | Time stamp       |
|----------|-------|---|---------------------------------|------------------|
| 2        | 0     | ("densified dielectric").PN.  | USPAT;<br>US-PGPUB;<br>EPO; JPO | 2002/07/18 16:18 |
| 7        | 0     | ("densified").PN.   | USPAT;<br>US-PGPUB;<br>EPO; JPO | 2002/07/18 17:15 |
| 12       | 0     | ("densified").PN.   | USPAT                           | 2002/07/18 17:15 |
| 13       | 8939  | densification   | USPAT                           | 2002/07/18 17:15 |
| 14       | 71    | densification near dielectric   | USPAT                           | 2002/07/18 17:16 |
| 15       | 616   | densification same dielectric   | USPAT                           | 2002/07/18 17:15 |
| 16       | 25    | (densification near dielectric) and plasma  | USPAT                           | 2002/07/18 17:22 |
| 17       | 697   | "low k dielectric"  | USPAT;<br>US-PGPUB;<br>EPO; JPO | 2002/07/18 17:23 |
| 22       | 105   | "low k dielectric" same "etch stop"   | USPAT;<br>US-PGPUB;<br>EPO; JPO | 2002/07/18 17:38 |
| 27       | 1     | 6054379.pn.   | USPAT                           | 2002/07/18 17:48 |
| 28       | 271   | treat\$3 near dielectric  | USPAT;<br>US-PGPUB;<br>EPO; JPO | 2002/07/18 17:49 |
| 33       | 87    | (treat\$3 near dielectric) and plasma   | USPAT;<br>US-PGPUB;<br>EPO; JPO | 2002/07/18 17:53 |
| 38       | 11    | ((treat\$3 near dielectric) and plasma) and "etch stop"   | USPAT;<br>US-PGPUB;<br>EPO; JPO | 2002/07/18 17:56 |
| 43       | 2     | 5314845.pn.   | USPAT;<br>US-PGPUB;<br>EPO; JPO | 2002/07/18 17:58 |
| 48       | 2     | 5915203.pn.   | USPAT;<br>US-PGPUB;<br>EPO; JPO | 2002/07/18 18:00 |
| 53       | 2     | ("6303047" "6365528").pn.   | USPAT;<br>US-PGPUB;<br>EPO; JPO | 2002/07/18 18:06 |
| 58       | 44591 | silicon with carbide  | USPAT;<br>US-PGPUB;<br>EPO; JPO | 2002/07/18 18:06 |
| 63       | 42528 | silicon with carbon   | USPAT;<br>US-PGPUB;<br>EPO; JPO | 2002/07/18 18:07 |
| 68       | 73891 | (silicon with carbide) or (silicon with carbon)   | USPAT;<br>US-PGPUB;<br>EPO; JPO | 2002/07/18 18:07 |
| 73       | 19286 | ((silicon with carbide) or (silicon with carbon)) same (plasma densified plasma Hydrogen He Helium Ar Argon NH3 ammonia N2 nitrogen)                          | USPAT;<br>US-PGPUB;<br>EPO; JPO | 2002/07/18 18:09 |
| 78       | 189   | ((silicon with carbide) or (silicon with carbon)) same (plasma densified plasma Hydrogen He Helium Ar Argon NH3 ammonia N2 nitrogen) and "low k"              | USPAT;<br>US-PGPUB;<br>EPO; JPO | 2002/07/18 18:10 |
| 83       | 167   | ((silicon with carbide) or (silicon with carbon)) same (plasma densified plasma Hydrogen He Helium Ar Argon NH3 ammonia N2 nitrogen) and "low k") and etch\$3 | USPAT;<br>US-PGPUB;<br>EPO; JPO | 2002/07/18 18:10 |